



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	RDS(ON) max	Ι _D T _A = +25°C
	$77m\Omega@V_{GS} = -10V$	-3.5A
-30V	$95m\Omega@V_{GS} = -4.5V$	-3.0A
	150mΩ@ V_{GS} = -2.5V	-2.4A

Description and Applications

This MOSFET has been designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

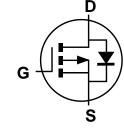
Mechanical Data

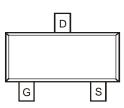
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(C)
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)



SOT23

Top View





Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3130LQ-7	SOT23	3000/Tape & Reel

Equivalent Circuit

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Notes:

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



 $\begin{array}{l} P5S = Product Type Marking Code \\ YM or \overline{Y}M = Date Code Marking \\ Y or \overline{Y} = Year (ex: D = 2016) \\ M = Month (ex: 9 = September) \end{array}$

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		E	F	F G		H I		J		K	
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	1	5	6	7	8	Q	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage		V _{GSS}	±12	V	
	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-3.5 -2.6	A
Continuous Drain Current (Note 6) V _{GS} = -4.5V	t<10s	T _A = +25°C T _A = +70°C	ID	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Curren	t (Note 6)	ls	-1.6	A	
Pulsed Drain Current (10µs pulse, duty cycle = 1%		I _{DM}	-20	A	

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Dower Dissinction (Note 6)	T _A = +25°C	T _A = +25°C		W	
Total Power Dissipation (Note 6)	T _A = +70°C	PD	0.4	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	184	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ heta JA}$	115	C/W	
Total Dower Dissinction (Note 7)	T _A = +25°C	D	1.3	W	
Total Power Dissipation (Note 7)	T _A = +70°C	PD	0.8		
Thermal Desistance, Junction to Ambient (Note 7)	Steady State	P	94	°C/W	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{ heta JA}$	61		
Thermal Resistance, Junction to Case		$R_{ ext{ heta}JC}$	25		
Operating and Storage Temperature Range		TJ. TSTG	-55 to +150	°C	

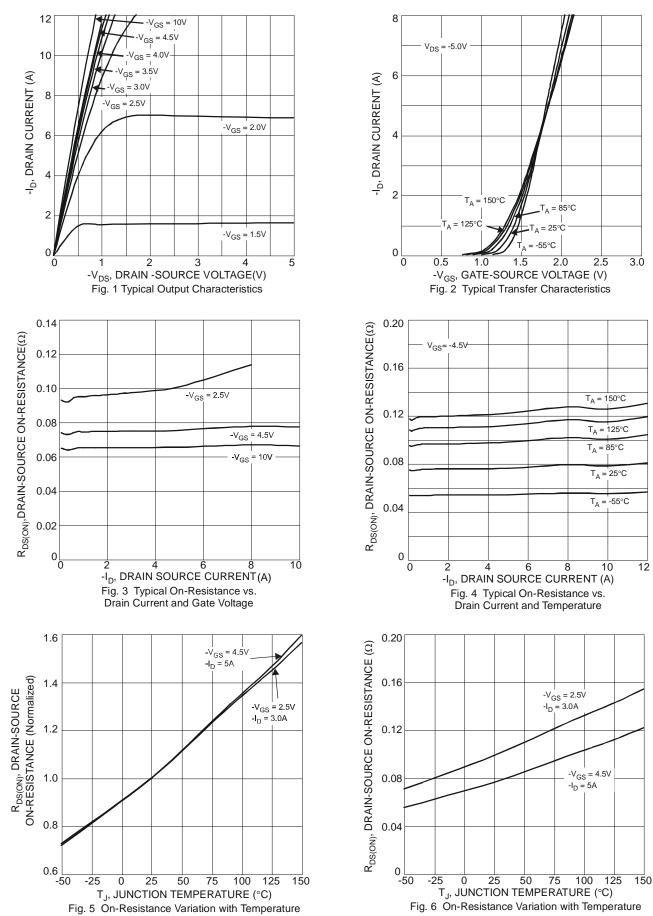
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						÷
Drain-Source Breakdown Voltage	BV _{DSS}	-30		_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						÷
Gate Threshold Voltage	V _{GS(TH)}	-0.6	_	-1.3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
			59	77		$V_{GS} = -10V, I_D = -4.2A$
Static Drain-Source On-Resistance	R _{DS(ON)}		73	95	mΩ	$V_{GS} = -4.5V, I_D = -4A$
			115	150		$V_{GS} = -2.5V, I_D = -3A$
Forward Transconductance	g fs		8	_	S	$V_{DS} = -5V, I_D = -4A$
Source-Drain Diode Forward Voltage	V _{SD}	_	-0.8	-1.25	V	$V_{GS} = 0V, I_{S} = -3.0A$
DYNAMIC CHARACTERISTICS (Note 9)						÷
Input Capacitance	Ciss		432	864	pF	
Output Capacitance	Coss		87	174	pF	[−] V _{DS} = -15V, V _{GS} = 0V −f = 1.0MHz
Reverse Transfer Capacitance	Crss		62	124	pF	1 - 1.00012
Gate Resistance	R _G		4.04	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 9)						
Total Gate Charge	Q_{G}		5.9	11.8		$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A$
Total Gale Gharge	QG	_	12	24	nC	$V_{DS} = -15V, V_{GS} = -10V, I_D = -4.0A$
Gate-Source Charge	Q _{GS}		1.0	2.0	10	
Gate-Drain Charge	Q _{GD}	_	3.1	6.2		$V_{DS} = -15V, V_{GS} = -4.5V, I_D = -4.0A$
Turn-On Delay Time	t _{D(ON)}		4.6	9.2		
Rise Time	t _R	_	6.5	13.0	20	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{D(OFF)}		27.8	55.6	ns	$I_D = -1A, R_G = 6.0\Omega$
Fall Time	t _F		15.0	30.0		

6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing

Notes:

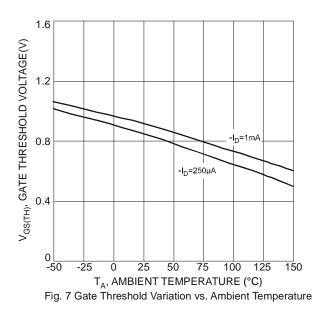


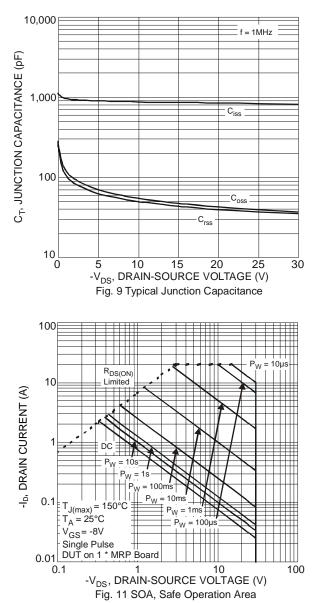


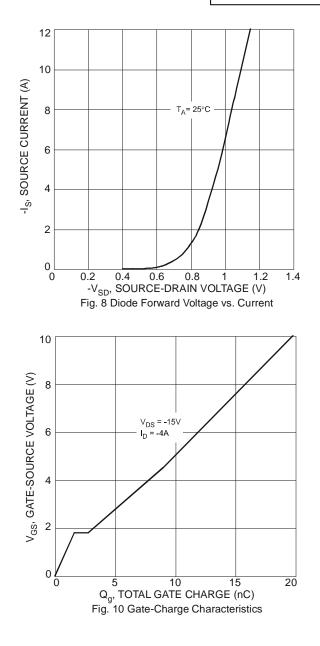
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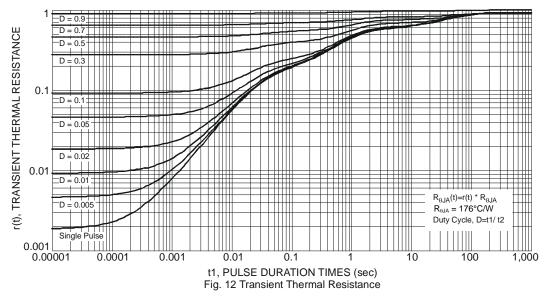






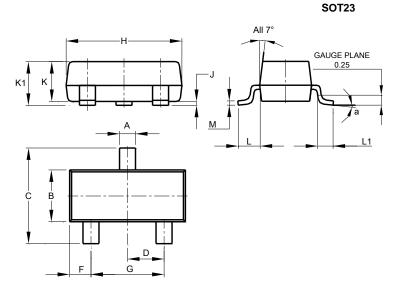






Package Outline Dimensions

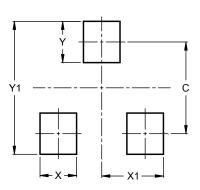
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SO	T23	
Dim	Min	Max	Тур
Α	0.37	0.51	0.40
В	1.20	1.40	1.30
С	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
Н	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
М	0.085	0.150	0.110
а	0°	8°	
All	Dimens	ions in	mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

DMP3130LQ Document number: DS38728 Rev. 1 - 2



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